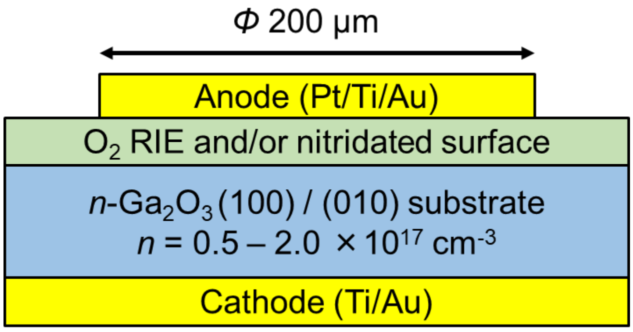
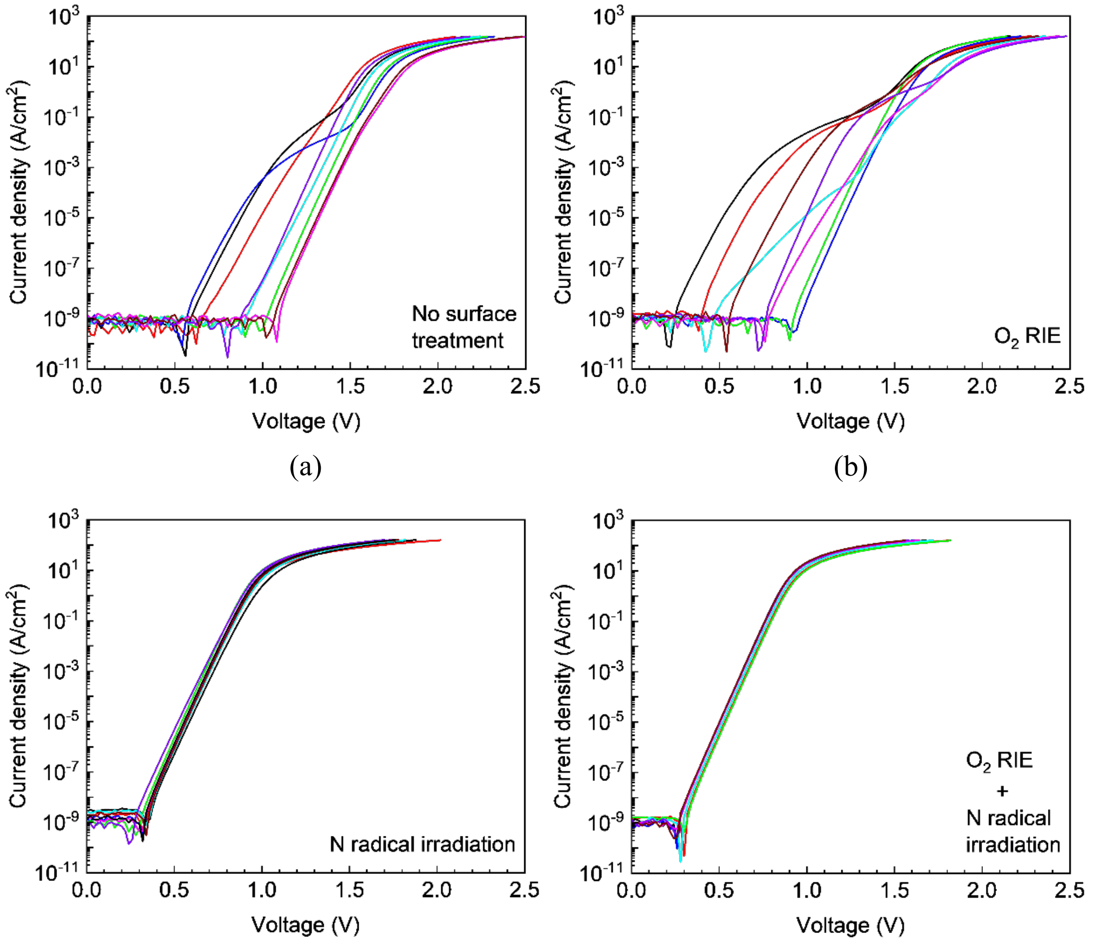


Figure 1 Cross-sectional schematic of β-Ga_2O_3 SBD structures.



(a) (b)

(c) (d)

Figure 2 Forward *J*–*V* characteristics of β-Ga_2O_3 (100) SBDs fabricated on four different treated substrates: (a) no surface treatment, (b) O_2 RIE, (c) N radical irradiation, (d) O_2 RIE followed by N radical irradiation.